crystallizing the amorphous silicon layer by applying thermal treatment and electric field to the resultant substrate,

wherein the thin film transistor having crystallized amorphous silicon layer is formed at each of the plurality of pixels.

14. A method of fabricating a thin film transistor for a liquid crystal display having a plurality of pixels comprising:

forming a first amorphous silicon layer as an active layer on a glass substrate;

forming a gate insulating layer and a second amorphous silicon layer as a gate electrode on the first amorphous silicon layer;

doping impurities of a first conductive type in the first and second amorphous silicon layers;

forming a metal layer on the doped portions of the first and second amorphous silicon layers; and

crystallizing the first and second amorphous silicon layers by performing heat treatment and applying electric filed on the resultant substrate,

wherein the thin film transistor having crystallized amorphous silicon layer is formed at each of the plurality of pixels.

25. A method of fabricating a thin film transistor for a liquid crystal display having a plurality of pixels comprising:

forming an amorphous silicon layer as an active layer on a glass substrate;

forming a gate insulating layer and a gate electrode on the amorphous silicon layer;

forming a metal layer on exposed portions of the amorphous silicon layer;

doping impurities of a first conductive type in the amorphous silicon layer after the metal layer is formed; and

crystallizing the amorphous silicon layer by applying thermal treatment and an electric field to the resultant substrate,

wherein the thin film transistor having crystallized amorphous silicon layer is formed at each of the plurality of pixels.